

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

- A1
1. (Currently Amended) A fabrication method for integrating a plurality of heterogeneous circuit devices in a single substrate, comprising:
- providing a substrate;
 - forming a first protective layer over the substrate;
 - removing a portion of the first protective layer to expose a first portion of the substrate;
 - ion implanting a high voltage well of a first circuit device in the first portion of the substrate using the partially removed first protective layer;
 - forming a second protective layer over at least the first portion of the substrate;
 - removing a second portion of the ~~second~~ first protective layer to expose a second portion of the substrate; and
 - ion implanting a first low voltage well of a second circuit device in the second portion of the substrate using the partially removed first protective layer and the second protective layer.
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